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LED Display Product Data Sheet LTP-757KR

Spec No.: DS30-2000-062

Effective Date: 01/09/2001

Revision: -

LITE-ON DCC

RELEASE

BNS-OD-FC001/A4

FEATURES

- * 0.7INCH (17.22mm) DIGIT HEIGHT.
- * CONTINUOUS UNIFORM SEGMENTS.
- * LOW POWER REQUIREMENT.
- * EXCELLENT CHARACTERS APPEARANCE.
- * HIGH BRIGHTNESS & HIGH CONTRAST.
- * WIDE VIEWING ANGLE.
- * SOLID STATE RELIABILITY.
- * CATEGORIZED FOR LUMINOUS INTENSITY.

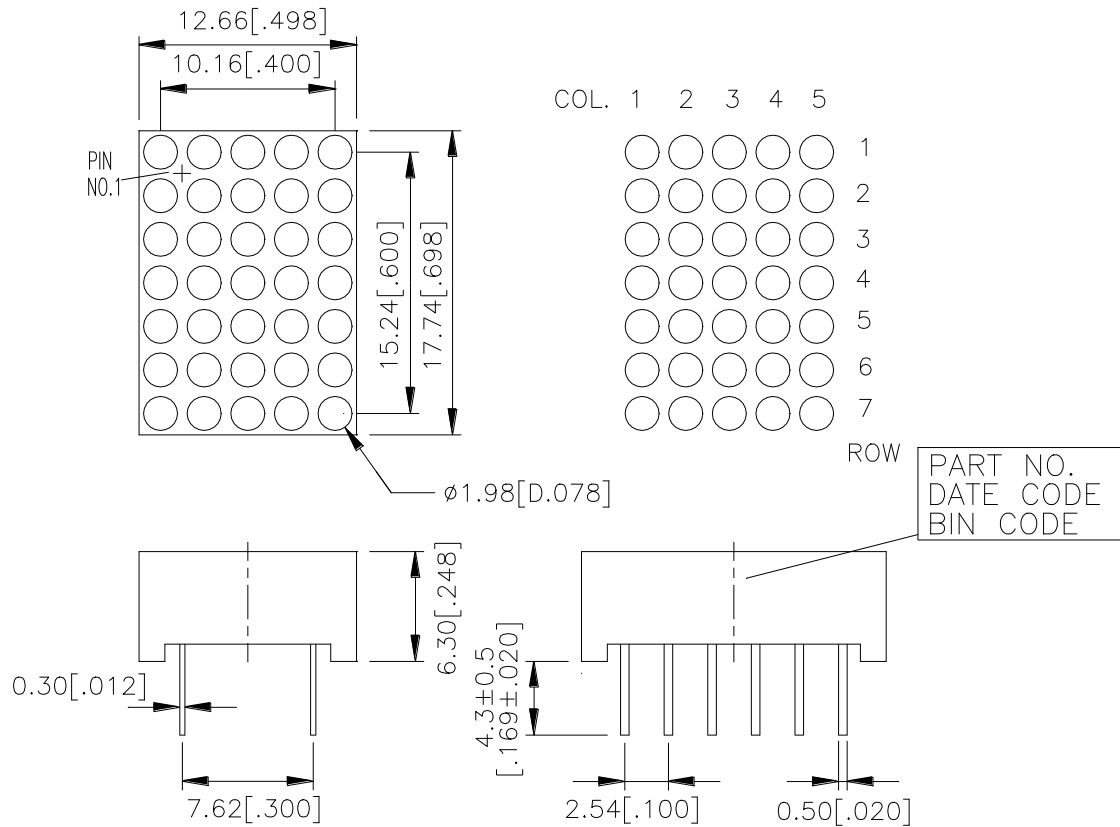
DESCRIPTION

The LTP-757KR is a 0.7inch (17.22mm) matrix height 5 x 7 dot matrix display. This device utilizes AlInGaP Super Red LED chips, which are made from AlInGaP on a non-transparent GaAs substrate, and has a gray face and white dots.

DEVICE

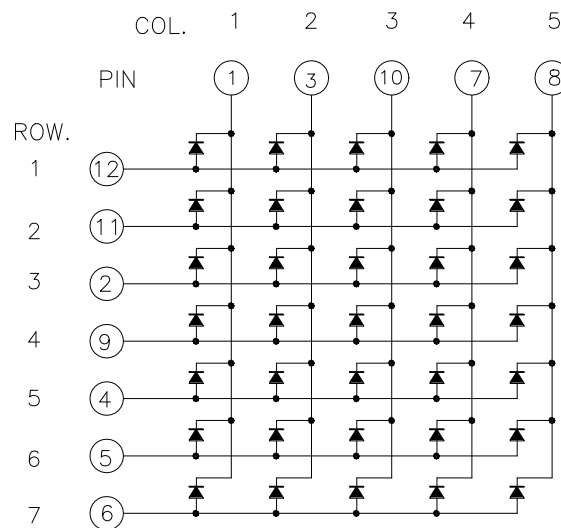
PART NO.	DESCRIPTION
AlInGaP SUPER RED	Cathode Column
LTP-757KR	Anode Row

PACKAGE DIMENSIONS



NOTES: All dimensions are in millimeters. Tolerances are ± 0.25 -mm (0.01^o) unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



PIN CONNECTION

No.	CONNECTION
1	CATHODE COLUMN 1
2	ANODE ROW 3
3	CATHODE COLUMN 2
4	ANODE ROW 5
5	ANODE ROW 6
6	ANODE ROW 7
7	CATHODE COLUMN 4
8	CATHODE COLUMN 5
9	ANODE ROW 4
10	CATHODE COLUMN 3
11	ANODE ROW 2
12	ANODE ROW 1

ABSOLUTE MAXIMUM RATING AT T_A=25°C

PARAMETER	MAXIMUM RATING	UNIT
Average Power Dissipation Per dot	33	mW
Peak Forward Current Per dot	90	mA
Average Forward Current Per dot	13	mA
Derating Linear From 25 ⁰ C Per dot	0.17	mA/ ⁰ C
Reverse Voltage Per dot	5	V
Operating Temperature Range	-35 ⁰ C to +85 ⁰ C	
Storage Temperature Range	-35 ⁰ C to +85 ⁰ C	
Solder Temperature 1/16 inch Below Seating Plane for 3 Seconds at 260 ⁰ C		

ELECTRICAL / OPTICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity	I _v	1650	3400		μcd	I _F =32mA , 1/16Duty
Peak Emission Wavelength	λ _p		639		nm	I _F =20mA
Spectral Line Half-Width	Δλ		20		nm	I _F =20mA
Dominant Wavelength	λ _d		631		nm	I _F =20mA
Forward Voltage Per dot	V _F		2.0	2.6	V	I _F =20mA
Reverse Current Per dot	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =32mA , 1/16Duty

Note: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (Commision Internationale De L'Eclairage) eye-response curve.

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

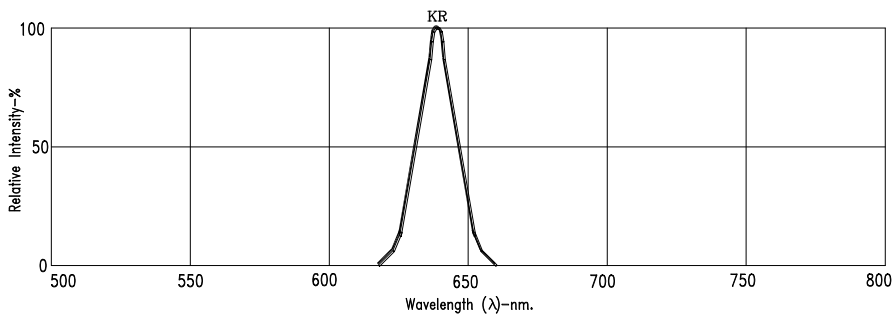


Fig1. RELATIVE INTENSITY VS. WAVELENGTH

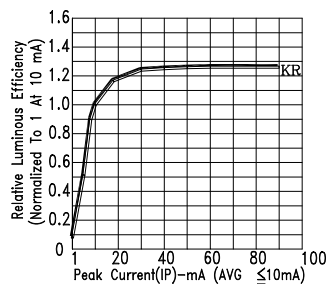


Fig2. RELATIVE LUMINOUS EFFICIENCY (LUMINOUS INTENSITY PER UNIT CURRENT) VS. PEAK CURRENT

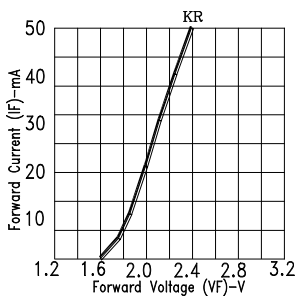


Fig3. FORWARD CURRENT VS. FORWARD VOLTAGE

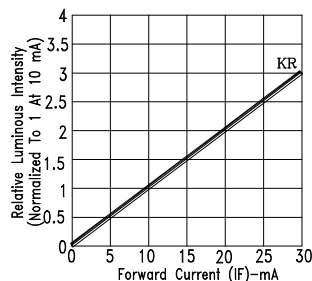


Fig4. RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT

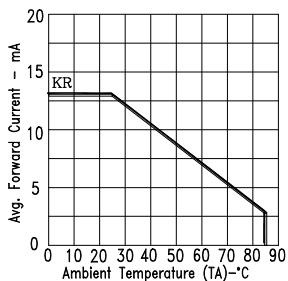


Fig5. MAX AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE.

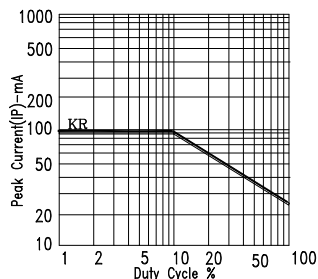


Fig6. MAX PEAK CURRENT VS. DUTY CYCLE % (REFRESH RATE 1KHz)

NOTE: KR=AlInGaP SUPER RED